

#### **Discription**

The ESD8D5.0 is designed to protect voltage sensitive components from ESD. Excellent clamping capability, low leakage, and fast response time provide best in class protection on designs that are exposed to ESD. Because of its small size, it is suited for use in cellular phones, MP3 players, digital cameras and many other portable applications where board space is at a premium.

### **Applications**

- I Cellular phones audio
- I MP3 players
- I Digital cameras
- I Portable applicationss
- I mobile telephone

#### **Features**

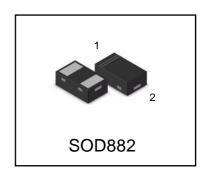
- Small Body Outline Dimensions: 0.039" x 0.024"(1.0 mm x 0.60 mm)
- Low Body Height: 0.020" (0.50 mm)
- Stand-off Voltage: 3.3 V 12 V
- ı Low Leakage
- Response Time is Typically < 1 ns
- ESD Rating of Class 3 (> 16 kV) per Human Body Model
- IEC61000-4-2 Level 4 ESD Protection
- These are Pb-Free Devices
- We declare that the material of product compliance with RoHS requirements.
- S- Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

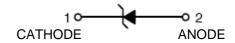
#### **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit
IEC 61000-4-2 (ESD) Air discharge Contact discharge		±15 ±8	kV kV
ESD Voltage Per Human Body Model		16	kV
Total Power Dissipation on FR-5 Board (Note 1)	PD	150	mW
@ T <sub>A</sub> =25℃			
Junction and Storage Temperature Range	TJ,TSTG	-55 to 150	$^{\circ}$
Lead Solder Temperature – Maximum (10	TL	260	$^{\circ}$
Second Duration)			

Stresses exceeding Maximum Ratings may damage the device. Maximum Rating are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. FR-5 = 1.0\*0.75\*0.62 in.



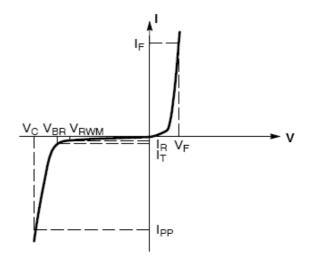




#### **ELECTRICAL CHARACTERISTICS**

(T<sub>A</sub> = 25°C unless otherwise noted)

Symbol	Parameter
I <sub>PP</sub>	Maximum Reverse Peak Pulse Current
Vc	Clamping Voltage @ I <sub>PP</sub>
$V_{RWM}$	Working Peak Reverse Voltage
I <sub>R</sub>	Maximum Reverse Leakage Current @ V <sub>RWM</sub>
V <sub>BR</sub>	Breakdown Voltage @ I <sub>T</sub>
I <sub>T</sub>	Test Current
I <sub>F</sub>	Forward Current
V <sub>F</sub>	Forward Voltage @ I <sub>F</sub>
P <sub>pk</sub>	Peak Power Dissipation
С	Max. Capacitance @V <sub>R</sub> = 0 and f = 1 MHz



Uni-Directional TVS

ELECTRICAL CHARACTERISTICS (T<sub>A</sub>=25°C unless otherwise noted, VF=0.9V Max. @ IF=10Ma for all types)

Device	$V_{RWM}$	I <sub>R</sub>	$V_{BR}$	Ι <sub>Τ</sub>	I <sub>PP</sub>	Vc	$P_{PK}$	С	
	(V)	( µ A)	(V)	(mA)	(A)	(V)	(W)	(pF)	
		@	@ I <sub>T</sub>			@ Max I <sub>PP</sub>	(8*20 µs)		
		$V_{RWM}$	(Note 2)		(Note 3)	(Note 3)			
	Max	Max	Min		Max	Max	Тур	Тур	
ESD8D3.3	3.3	2.5	5.0	1.0	9.8	10.4	102	80	
ESD8D5.0	5.0	1.0	6.2	1.0	8.7	12.3	107	65	
ESD8D12	12	1.0	13.3	1.0	5.9	23.7	140	30	

Other voltage available upon request.

- 3. Surge current waveform per Figure 3.

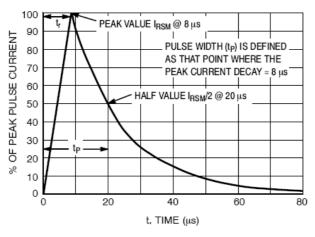
# MSV SEMI

#### TYPICAL CHARACTERISTICS BREAKDOWN VOLTAGE (VOLTS) (VZ @ IZ) 7.4 7.3 7.2 7.1 7.0 6.9 6.8 6.7 6.6 6.5 6.4 6.3 +25 +150TEMPERATURE (°C)

20 18 16 14 12 10 8 6 4 2 0 -55 +25 +150 TEMPERATURE (°C)

Figure 1. Typical Breakdown Voltage versus Temperature

Fig 2. Typical Leakage Current versus
Temperature



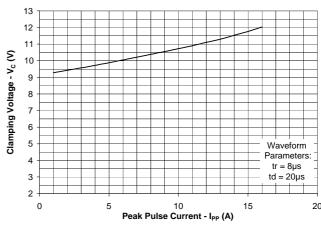
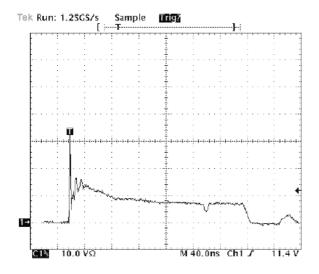


Figure 3. 8\*20 µs Pulse Waveform

Fig 4. Normalized Junction Capacitance Voltage vs. Reverse Voltage



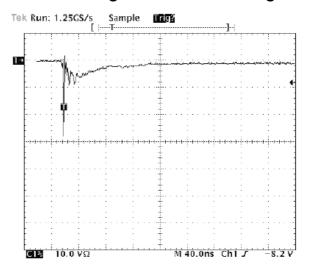


Figure 5. Positive 8kV contact per IEC 61000-4-2-ESD8D5.0

Fig 6. Negative 8kV contact per IEC 61000-4-2-ESD8D5.0

## **SOD882**

DIMENSION OUTLINE:

Unit:mm

